PRODUCT / PROCESS CHANGE NOTIFICATION

1. PCN basic data		
1.1 Company STMicroelectronics International N.V		STMicroelectronics International N.V
1.2 PCN No.		AMS/15/9514
1.3 Title of PCN		Product Change Notification on new material set in ST Bouskoura for AMS products in SO8 and SO14 packages
1.4 Product Category		See product list
1.5 Issue date		2015-11-18

2. PCN Team		
2.1 Contact supplier		
2.1.1 Name	ROBERTSON HEATHER	
2.1.2 Phone	+1 8475853058	
2.1.3 Email	heather.robertson@st.com	
2.2 Change responsibility		
2.2.1 Product Manager	Andrea Mario ONETTI	
2.1.2 Marketing Manager	Lionel GRILLO	
2.1.3 Quality Manager	Jean-Marc BUGNARD	

3. Change		
3.1 Category	3.2 Type of change	3.3 Manufacturing Location
	New direct material part number (same supplier, different supplier or new supplier), lead frame, resin, wire,)	ST Bouskoura (Morocco)

4. Description of change		
Old New		
4.1 Description	Molding compound = Sumitomo G700K / Sumitomo G630AY	Molding compound = Sumitomo G700KC
4.2 Anticipated Impact on form,fit, function, quality, reliability or processability?	No impact on form, fit, function, reliability, or processability	

5. Reason / motivation for change		
Progressing on the activities related to quality improvement, ST is glad to announce a new material set for AMS products in SO8 and SO14 packages produced in ST Bouskoura.		
5.2 Customer Benefit	QUALITY IMPROVEMENT	

6. Marking of parts / traceability of change		
6.1 Description	Finish good code	

7. Timing / schedule		
7.1 Date of qualification results	2015-11-05	
7.2 Intended start of delivery	2016-01-05	
7.3 Qualification sample available?	Upon Request	

8. Qualification / Validation			
8.1 Description 9514_Qual report SO Bouskoura_new.pdf			
8.2 Qualification report and qualification results	Available (see attachment)	Issue Date	2015-11-18

9. Attachments (additional documentations)

9514PpPrdtLst.pdf 9514_Qual report SO Bouskoura_new.pdf

10. Affected parts		
10. 1 Current		10.2 New (if applicable)
10.1.1 Customer Part No	10.1.2 Supplier Part No	10.1.2 Supplier Part No
LF247DT	LF247DT	
LF253DT	LF253DT	
LF351DT	LF351DT	
LF353DT	LF353DT	
LM124DT	LM124DT	
	LM139ADT	
	LM139DT	
	LM158DT	
	LM193DT	
LM201ADT	LM201ADT	
LM211DT	LM211DT	
LM219DT	LM219DT	
LM224DT	LM224DT	
LM234DT	LM234DT	
LM235DT	LM235DT	
LM239ADT	LM239ADT	
LM248DT	LM248DT	
LM258ADT	LM258ADT	
LM258DT	LM258DT	
	LM258WDT	
LM2901DT	LM2901DT	
LM2902DT	LM2902DT	
LM2903DT	LM2903DT	
	LM2903WDT	
LM2904DT	LM2904DT	
LM2904WHDT	LM2904WHDT	
LM293ADT	LM293ADT	
LM293DT	LM293DT	
LM311DT	LM311DT	
LM319DT	LM319DT	
LM324ADT	LM324ADT	
LM324DT	LM324DT	
LM334DT	LM334DT	
LM335DT	LM335DT	
LM339ADT	LM339ADT	
LM358ADT	LM358ADT	
LM358DT	LM358DT	
LM393ADT	LM393ADT	
LM393DT	LM393DT	
LM833DT	LM833DT	
LMV324IDT	LMV324IDT	
	LMV324LIDT	
	LMV339IDT	
LMV358IDT	LMV358IDT	

	LMV358LIDT	
	LMV393IDT	
	LMV822AIDT	
	LMV822IDT	
	LMV824AIDT	
	LMV824IDT	
	LMX324IDT	
1144700405	LMX358IDT	
M41T00M6F	M41T00M6F	
M41T00SM6F	M41T00SM6F	
M41T0M6F	M41T0M6F	
M41T11M6F	M41T11M6F	
M41T56M6F	M41T56M6F	
M41T80M6F	M41T80M6F	
M41T81M6F	M41T81M6F	
M41T81SM6F	M41T81SM6F	
	M41T82RM6F	
	M41T82SM6F	
	M41T82ZM6F	
MC1458ID	MC1458ID	
MC3303DT	MC3303DT	
MC33078DT	MC33078DT	
MC33079DT	MC33079DT	
MC33171DT	MC33171DT	
MC33172DT	MC33172DT	
MC33174DT	MC33174DT	
MC3403DT	MC3403DT	
MC4558CDT	MC4558CDT	
MC4558IDT	MC4558IDT	
STLM75M2F-ND	STLM75M2F	
497-3825-2-ND	STM690RM6F	
497-3829-2-ND	STM703M6F	
497-3832-2-ND	STM704SM6F	
497-3833-2-ND	STM704TM6F	
497-3834-2-ND	STM705M6F	
497-3835-2-ND	STM706M6F	
	STM706PAM6F	
497-3838-2-ND	STM706SM6F	
	STM706TAM6F	
497-3839-2-ND	STM706TM6F	
	STM708RAM6F	
	STM708SAM6F	
497-3843-2-ND	STM708SM6F	
497-3845-2-ND	STM795RM6F	
497-3852-2-ND	STM802TM6F	
497-3863-2-ND	STM813LM6F	
497-3864-2-ND	STM817LM6F	
497-3867-2-ND	STM818MM6F	
	STTS75M2F	
	TL061CDT	
	TL061IDT	

TL062ACDT	
TL062CDT	
TL064CDT	
TL064IDT	
TL071IDT	
TL072ACDT	
TL072BIDT	
TL072CDT	
TL072IDT	
TL074ACDT	
TL074CDT	
TL081IDT	
TL082BCDT	
TL082CDT	
TL082IDT	
TL084ACDT	
TL084AIDT	
TL084BCDT	
TL084BIDT	
TL084CDT	
TL084IDT	
TS1852IDT	
TS1854IDT	
TS271CDT	
TS272AIDT	
TS272BIDT	
TS272CDT	
TS272IDT	
TS274ACDT	
TS274AIDT	
TS27L2BIDT	
TS27L2CDT	
TS27L4AIDT	
TS27L4IDT	
TS27M2CDT	
TS27M4CDT	
TS3022IDT	
TS332IDT	
TS334IDT	
TS339CDT	
TS339IDT	
TS3702CDT	
TS3702IDT	
TS3704CDT	
TS3704IDT	
TS372CDT	
TS372IDT	
TS374CDT	
TS393CDT	
TS393IDT	
TS461CDT	

I	
TS462CDT	
TS464CDT	
TS482IDT	
TS512AIDT	
TS514AIDT	
TS514IDT	
TS522IDT	
TS524IDT	
TS831-4IDT	
TS831-5IDT	
TS862IDT	
TS884IDT	
TS912AIDT	
TS912BIDT	
TS912IDT	
TS921IDT	
TS9222IDT	
TS9224IDT	
TS922AIDT	
TS922IDT	
TS924AIDT	
TS924IDT	
TS932IDT	
TS934IDT	
TS942AIDT	
TS942IDT	
TS944AIDT	
TS952IDT	
TS954IDT	
TS971IDT	
TS972IDT	
TS974IDT	
TSC1031IDT	
TSC103IDT	
TSH22IDT	
TSH24IDT	
TSV324IDT	
TSV358AIDT	
TSV358IDT	
TSV612IDT	
TSV6192AIDT	
TSV6192IDT	
TSV622AIDT	
TSV6292AIDT	
TSV6292IDT	
TSV632AIDT	
TSV632IDT	
TSV6392AIDT	
TSV6392IDT	
TSV854AIDT	
TSV854IDT	

TSV912AIDT	
TSV912IDT	
TSV914AIDT	
TSV914IDT	
TSV992AIDT	
TSV992IDT	
TSX3702IDT	
TSX922IDT	
TSX9292IDT	
UA741CDT	
UA741IDT	
TS556IDTTR	

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PRODUCT/PROCESS CHANGE NOTIFICATION

PCN AMS/15/9514

Analog, MEMS and Sensors Group

New material set in ST Bouskoura for AMS products in SO8 and SO14 packages

October 2015 5



WHAT:

Progressing on the activities related to quality continuous improvement, ST is glad to announce a new material set for AMS products in SO8 and SO14 packages produced in ST Bouskoura. Please find more information related to material change in the table here below.

	Current process	Modified process	Comment
Material			
Diffusion location	ST Ang Mo Kio (Singapore)/ UMC	ST Ang Mo Kio (Singapore)/ UMC	No change
Assembly location	ST Bouskoura	ST Bouskoura	No change
Molding compound	Sumitomo G700K / Sumitomo G630AY	Sumitomo G700KC	To solve some sporadic delamina- tion on lead issues sawn in produc- tion. Move to High reliability com- pound
Die attach	Ablestick 8601-S25	Ablestick 8601-S25	No change
Leadframe	rame Copper preplated NiPdAgAu Copper preplated ag spot		No change
Wire	Copper 1 mil	Copper 1 mil	No change
Plating	NiPdAgAu Sn	Sn	No change

Samples of vehicle test are available now and other samples will be launched upon customer's request. Please submit requests for samples within 30 days of this notification.

WHY:

This material change will contribute to ST's continuous quality product improvement and ensure a consistent assembly process through all the SO production lines.

HOW:

The qualification program consists mainly of comparative electrical characterization and reliability tests.

You will find here after the qualification test plan which summarizes the various test methods and conditions that ST uses for this qualification program.

WHEN:

The new material set will be implemented for AMS products in Q1/2016 in Bouskoura.



Marking and traceability:

Unless otherwise stated by customer's specific requirement, the traceability of the parts assembled with the new material set will be ensured by new internal sales type, date code and lot number.

The changes here reported will not affect the electrical, dimensional and thermal parameters keeping unchanged all the information reported on the relevant datasheets.

There is -as well- no change in the packing process or in the standard delivery quantities.

Lack of acknowledgement of the PCN within 30 days will constitute acceptance of the change. After acknowledgement, lack of additional response within the 90 day period will constitute acceptance of the change (Jedec Standard No. 46-C).

Shipments may start earlier with the customer's written agreement.



Reliability Report

New Halogen free material set for SO in ST Bouskoura

General Information

Product Line 0393, 0339, 0084

Dual comparator bipolar,
Product Description Quad comparator bipolar, quad

Jfetl op amp

LM2903YDT, LM2901YDT,

Product GroupAMSProduct divisionVMAPackageSO8/14Silicon Process technologyBipolar, Jfet

Loca	tions
Wafer fab	ST Singapore,
Assembly plant	ST Bouskoura (Morocco)
Reliability Lab	ST Grenoble, ST Bouskoura

Note: This report is a summary of the reliability trials performed in good faith by STMicroelectronics in order to evaluate the potential reliability risks during the product life using a set of defined test methods.

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1 APPLICABLE AND REFERENCE DOCUMENTS

Document reference	Short description
AEC-Q100	Stress test qualification for automotive grade integrated circuits
AEC-Q101	Stress test qualification for automotive grade discrete semiconductors
JESD47	Stress-Test-Driven Qualification of Integrated Circuits

2 GLOSSARY

DUT	Device Under Test
PCB	Printed Circuit Board
SS	Sample Size

3 RELIABILITY EVALUATION OVERVIEW

3.1 Objectives

To qualify a new molding compound for SO package in Bouskoura (Sumitomo G700KC which is an evolution of Sumitomo G700K already in use in Bouskoura) for AMS (Analog Mems & Sensor) group.

3.2 Conclusion

Qualification Plan requirements have been defined and today partially achieved. It is stressed that reliability tests have to show that the devices behave correctly against environmental tests (no failure). Moreover, the stability of electrical parameters during the accelerated tests have to demonstrate the ruggedness of the products and safe operation, which is consequently expected during their lifetime.



4 DEVICE CHARACTERISTICS

4.1 Device description

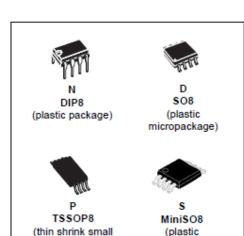
LM2903YDT



LM2903

Low-power dual voltage comparator

Datasheet - production data



micropackage)

Related products

· Automotive qualification

outputs

 See LM2903W for similar device with higher ESD performances

TTL, DTL, ECL, MOS, CMOS compatible

 See LM2903H for similar device with operating temperature up to 150 °C

Description

This device consists of two independent lowpower voltage comparators designed specifically to operate from a single supply over a wide range of voltages. Operation from split power supplies is also possible.

In addition, the device has a unique characteristic in that the input common-mode voltage range includes the negative rail even though operated from a single power supply voltage.

Features

outline package)

- Wide single supply voltage range or dual supplies +2 V to +36 V or ±1 V to ±18 V
- Very low supply current (0.4 mA) independent of supply voltage (1 mW/comparator at +5 V)

DFN8 2x2 mm (plastic micropackage)

- Low input bias current: 25 nA typ.
- Low input offset current: ±5 nA typ.
- Input common-mode voltage range includes negative rail
- Low output saturation voltage: 250 mV typ. (I_O = 4 mA)
- Differential input voltage range equal to the supply voltage



LM2901YDT,



LM2901

Low-power quad voltage comparator

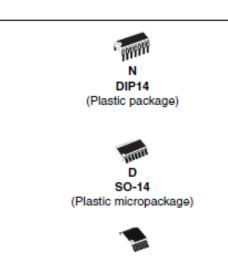
Features

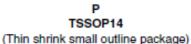
- Wide single supply voltage range or dual supplies for all devices: +2 V to +36 V or ±1 V to ±18 V
- Very low supply current (1.1 mA) independent of supply voltage (1.4 mW/comparator at +5 V)
- Low input bias current: 25 nA typ.
- Low input offset current: ±5 nA typ.
- Input common-mode voltage range includes negative rail
- Low output saturation voltage: 250 mV typ. (I_O = 4 mA)
- Differential input voltage range equal to the supply voltage
- TTL, DTL, ECL, MOS, CMOS compatible outputs

Description

This device consists of four independent precision voltage comparators, which are designed specifically to operate from a single supply over a wide range of voltages. Operation from split power supplies is also possible.

These comparators also have a unique characteristic in that the input common-mode voltage range includes the negative rail even though operated from a single power supply voltage.







QFN16 3x3 (Plastic micropackage)



TL084IYDT:



TL084, TL084A, TL084B

General purpose JFET quad operational amplifiers

Datasheet — production data

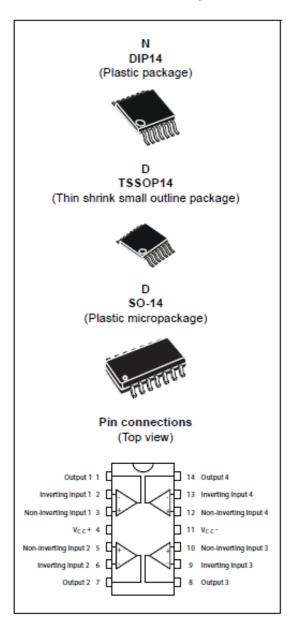
Features

- Wide common-mode (up to V_{CC}⁺) and differential voltage range
- Low input bias and offset current
- Output short-circuit protection
- High input impedance JFET input stage
- Internal frequency compensation
- Latch up free operation
- High slew rate: 16 V/µs (typical)

Description

The TL084, TL084A, and TL084B are high-speed, JFET input, quad operational amplifiers incorporating well matched, high voltage JFET and bipolar transistors in a monolithic integrated circuit.

The devices feature high slew rates, low input bias and offset currents, and low offset voltage temperature coefficient.





4.2 **Construction note**

	P/N LM2903YDT	P/N LM2901YDT	P/N TL084IYDT	
Wafer/Die fab. informa-				
tion				
Wafer fab manufacturing	ST Singapore	ST Singapore	ST Singapore	
location				
Technology	Bipolar	Bipolar	JFet	
Die finishing back side	RAW SILICON	RAW SILICON	RAW SILICON	
Die size (microns)	950 x 870 μm	1370x1270	2480 x 1460	
Bond pad metallization	AlSiCu	AlSiCu	AlSiCu	
layers				
Passivation type	Nitride	Nitride	P-VAPOX/NITRIDE	
Wafer Testing (EWS)				
information				
Electrical testing manu-	ST Singapore	ST Singapore	ST Singapore	
facturing location				
Tester	ASL1K	ASL1K	ASL1K	
Assembly information				
Assembly site	ST Bouskoura	ST Bouskoura	ST Bouskoura	
Package description	SO8	SO14	SO14	
Molding compound	EME G700KC	EME G700KC	EME G700KC	
Frame material	Cu	Cu	Cu	
Die attach process	Epoxy Glue	Epoxy Glue	Epoxy Glue	
Die attach material	8601S-25	8601S-25	8601S-25	
Wire bonding process	Thermosonic ball	Thermosonic ball	Thermosonic ball	
	bonding	bonding	bonding	
Wires bonding mate-	Cu 1 mil	Cu 1 mil	Cu 1 mil	
rials/diameters				
Lead finishing process	electroplating	electroplating	electroplating	
Lead finishing/bump sol-	Matte tin	Matte tin	Matte tin	
der material				
Final testing information				
Testing location	ST Bouskoura	ST Bouskoura	ST Bouskoura	
Tester	ASL1K	ASL1K	ASL1K	



5 TESTS RESULTS SUMMARY

5.1 **Test vehicle**

Lot #	Process/ Package	Product Line	Comments
1	Bipolar/SO8	0393	CZ53005LR
2	Bipolar/SO14	0339	CZ52405FR
3	JFet / So14	0084	CZ53306W

5.2 **Test plan and results summary**

						Failure/SS				
Test	PC	Std ref.	Conditions	SS		Lot 1 0393	Lot 2 0339	Lot 3 0084	Note	
					_	-		•	•	
		JESD22			168 H	0/78	0/78			
HTB	N	A-108	Tj = 150°C, BIAS		500 H	0/78	0/78			
		11 100			1000 H	78	0/78			
						6X0/77	3x0/77	77	(1)	
HTSL	N	JESD22	Ta = 150°C			6X0/77	3x0/77	77		
11102	1	A-103	14 100 0		1000 H	6X77	3x0/77	77		
					2000H					_
Package	Orie	ented Tests			I			1		
PC		JESD22 A-113	Drying 24 H @ 125°C Store 168 H @ Ta=85°C Rh=85% Over Reflow @ Tpeak=260°C 3 times		Final	PASS	PASS	PASS		
AC	Y	JESD22 A-102	Pa=2Atm / Ta=121°C		96 H	6x0/77	3x0/77	77	(1)	
		JESD22			100 cy	6x0/77	3x0/77	77	(1)	
TC	Y	JESD22 A-104	$Ta = -65^{\circ}C \text{ to } 150^{\circ}C$			6x0/77	3x0/77	77		
		A-104			500 cy	6x0/77	3x0/77	77		
		IECD22			168 H		0/78			
THB	Y	JESD22 A-101	$Ta = 85^{\circ}C, RH = 85\%, BIAS$		500 H		78			
		A-101			1000 H		78			
Other Te	sts									
		AEC Q101-								
ESD	N	001, 002 and 005	CDM			3	3	3		
SD	N		After ageing 8h and 16h			X	X			

⁽¹⁾ Additional split lot to cover the whole assembly variability



For reference, below the reliability assessment made on Sumitomo G700K

	P/N LM324DT	P/N TSV632IDT	P/N TSx922IDT	P/N TSX3702IDT	P/N TSX393IDT	P/N TSX3702IDT	P/N LM358DT
Wafer/Die fab. information							
Wafer fab manu- facturing location	AMJ9	Crolles	Agrate	Agrate	Agrate	Agrate	AMK6
Technology	Bipolar	HCMOS5LA	HVG8A	HVG8A	HVG8A	HVG8A	Bipolar
Process family	Bipolar	HCMOS5LA	HVG8A	HVG8A	HVG8A	HVG8A	Bipolar
Die finishing back side	Raw silicon						
Die size	1430x 1360 μm	1020 x 1090 μm	1700x1400 µm	1018x1238 μm	1018x1238 μm	1018x1238 μm	1070x1010 µm
Bond pad metal- lization layers	AlSiCu	AlCu	AlCu	AlCu	AlCu	AlCu	AlSiCu
Passivation type	Nitride	PSG + NITRIDE + PIX	HDP/TEOS/SiN /Polyimide	HDP/TEOS/SiN /Polyimide	HDP/TEOS/Si N/Polyimide	HDP/TEOS/Si N/Polyimide	Nitride
Wafer Testing (EWS) infor- mation							
Electrical testing manufacturing location	ST Singapore	ST Singa- pore	ST Singapore				
Tester	ASL1K						
Assembly in- formation							
Assembly site	Bouskoura						
Package descrip- tion	SO14	SO8	SO8	SO8	SO8	SO8	SO8
Molding com- pound	Sumitomo G700K						
Frame material	Cu						
Die attach pro- cess	Glue						
Die attach mate- rial	Abkestick 8601-S25						
Die pad size	75 x 75 μm²	75 x 75 μm²	75 x 75 μm²	75 x 75 µm²	75 x 75 μm²	75 x 75 µm²	75 x 75 µm²
Wire bonding process	Thermosonic Ball bonding						
Wires bonding materi- als/diameters	Cu 1 mil						
Lead finishing process	preplated						
Lead finish- ing/bump solder material	NiPdAgAu	NiPdAgAu	NiPdAgAu	NiPdAgAu	NiPdAgAu NiPdAgAu		NiPdAgAu
Final testing in- formation							
Testing location	Bouskoura						
Tester	ASL1K						



Test	PC	Std ref.	Conditions	Steps								Note
	. •	Ota ron	Conditions	Clope	Lot 1	Lot 2	Lot 3	Lot 4	Lot 5	Lot 6	Lot 7	110.0
		l		Die O	riented Te	sts						
		JESD22	Tj = 125°C, BIAS	168 H	0 / 78	0 / 78	0 / 78	0 / 78	0 / 78		0 / 78	
НТВ	N	A-108		500H	0 / 78	0 / 78	0 / 78		0 / 78	0 / 78	0 / 78	
				1000H	0 / 78	0 / 78	0 / 78		0 / 78		0 / 78	
		-		168 H	0 / 78	0 / 78			0 / 78		0 / 76	
HTSL	N	JESD22 A-103	Ta=150°C	500H	0 / 78	0 / 78			0 / 78		0 / 76	
		7. 100		1000H	0 / 78	0 / 78			0 / 78		0 / 76	
				Package	Oriented	Tests						
		JESD22	Drying 24 H @ 125°C		PASS	PASS	PASS	PASS	PASS	PASS	PASS	
PC		A-113	Store 168 H @ Ta=85°C Rh=85%	Final								
			Over Reflow @ Tpeak=260°C 3 times									
	Υ	JESD22	Pa=2Atm /	96 H								
AC		A-102	Ta=121°C	168 H	0 / 78	0 / 78			0 / 80		0 / 116	
	Υ	JESD22		100 cy							0 / 77	
TC		A-104	Ta = -65°C to 150°C	500 cy	0 / 78	0 / 78	0 / 78	0 / 80	0 / 78		0 / 77	
				1000 cy							0 / 77	
THB	Υ	JESD22	Ta = 85°C, RH =	168H	0 / 78	0 / 78			0 / 78		0 / 78	
IHB		A-101	85%, BÍAS	1000H	0 / 78	0 / 78			0 / 78		0 / 78	



	P/N TSH95IDT	P/N HCF4093BMTR	P/N TS393IDT	P/N TS912IDT	P/N TSV912IDT	P/N TS924IDT
Wafer/Die fab. infor- mation						
Wafer fab manufacturing location	AMK6	AMK6	AMK6	AMK6	UMC	AMK6
Technology	HF2CMOS	Metal Gate	HC1PA	HC1PA	HF5CMOS	HF2CMOS
Process family	HF2CMOS	Metal Gate	HC1PA	HC1PA	HF5CMOS	HF2CMOS
Die finishing back side	Raw silicon	Raw silicon	Raw silicon	Raw silicon	Raw silicon	Raw silicon
Die size	1990x2700 μm	1480x930 μm	1390x1010 μm	2630x1980 μm	1070x110 μm	1980x2450 µm
Bond pad metallization layers	AlSiCu	AlSi	AlSi	AlSi	AlCu	AlSiCu
Passivation type	P- VAPOX(SiO2) / NITRIDE (SiN)	P- VAPOX(SiO2) / NITRIDE (SiN)	P- VAPOX(SiO2) / NITRIDE (SiN)	P- VAPOX(SiO2) / NITRIDE (SiN)	P- VAPOX(SiO2) / NITRIDE (SiN)	P-VAPOX(SiO2) / NITRIDE (SiN)
Wafer Testing (EWS) in- formation						
Electrical testing manufacturing location	ST Singapore	ST Singapore	ST Singapore	ST Singapore	ST Singapore	ST Singapore
Tester	ASL1K	ASL1K	ASL1K	ASL1K	ASL1K	ASL1K
Assembly information						
Assembly site	Bouskoura	Bouskoura	Bouskoura	Bouskoura	Bouskoura	Bouskoura
Package description	SO16	SO14	SO8	SO8	SO8	SO14
Molding compound	Sumitomo G700K	Sumitomo G700K	Sumitomo G700K	Sumitomo G700K	Sumitomo G700K	Sumitomo G700K
Frame material	Cu	Cu	Cu	Cu	Cu	Cu
Die attach process	Glue	Glue	Glue	Glue	Glue	Glue
Die attach material	Abkestick 8601-S25	Abkestick 8601- S25	Abkestick 8601-S25	Abkestick 8601-S25	Abkestick 8601-S25	Abkestick 8601- S25
Wire bonding process	Thermosonic Ball bonding	Thermosonic Ball bonding	Thermosonic Ball bonding	Thermosonic Ball bonding	Thermosonic Ball bonding	Thermosonic Ball bonding
Wires bonding materials/diameters	Cu 1 mil	Cu 1 mil	Cu 1 mil	Cu 1 mil	Cu 1 mil	Cu 1 mil
Lead finishing process	preplated	preplated	preplated	preplated	preplated	preplated
Lead finishing/bump solder material	NiPdAgAu	NiPdAgAu	NiPdAgAu	NiPdAgAu	NiPdAgAu	NiPdAgAu
Final testing information						
Testing location	Bouskoura	Bouskoura	Bouskoura	Bouskoura	Bouskoura	Bouskoura
Tester	ASL1K	ASL1K	ASL1K	ASL1K	ASL1K	ASL1K



28-October-2015

Test	PC	Std ref.	Conditions	Steps	Failure/SS							Note
1631		Olu ICI.	Conditions	опера	Lot 1	Lot 2	Lot 3	Lot 4	Lot 5	Lot 6	Lot 7	Hote
				Die Orie	nted Tests			4				
		JESD22	Tj = 125°C, BIAS	168 H	0 / 78	0 / 78	0/78	78	0 / 78		0 / 78	
НТВ	N	A-108		500H	0 / 78	0 / 78	0/78		0 / 78	0 / 78	0 / 78	
				1000H	0 / 78	0 / 78	0 / 78		0 / 78		0 / 78	
				168 H	0 / 78	0 / 78			0 / 78		0 / 76	
HTSL	N	JESD22 A-103	Ta=150°C	500H	0 / 78	0 / 78			0 / 78		0 / 76	
		71.100		1000H	0 / 78	0 / 78			0 / 78		0 / 76	
	Package Oriented Tests											
		JESD22	Drying 24 H @ 125°C		PASS	PASS	PASS	PAS S	PASS	PASS	PASS	
PC		A-113	Store 168 H @ Ta=85°C Rh=85%	Final								
			Over Reflow @ Tpeak=260°C 3 times									
	Υ	JESD22	Pa=2Atm /	96 H								
AC		A-102	Ta=121°C	168 H	0 / 78	0 / 78			0 / 80		0 / 116	
	Υ	JESD22		100 cy							0 / 77	
TC		A-104	Ta = -65°C to 150°C	500 cy	0 / 78	0 / 78	0/78	0 / 80	0/78		0 / 77	
				1000 cy							0 / 77	
TUD	Υ	JESD22	Ta = 85°C, RH =	168H	0 / 78	0 / 78			0/78		0 / 78	
THB		A-101	85%, BIAS	1000H	0 / 78	0 / 78			0 / 78		0 / 78	

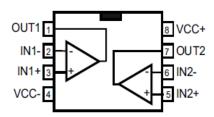


6 ANNEXES

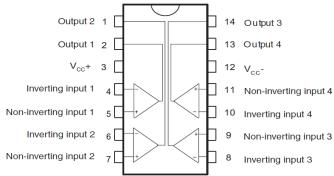
6.1 **Device details**

6.1.1 Pin connection

LM2903



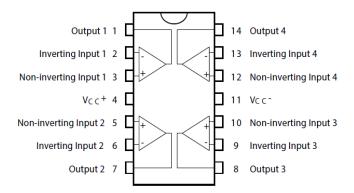
LM2901



TL084

Pin connections

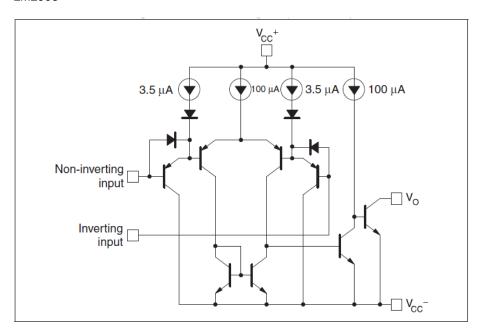
(Top view)



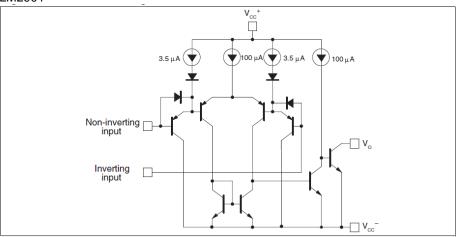


6.1.2 Block diagram

LM2903

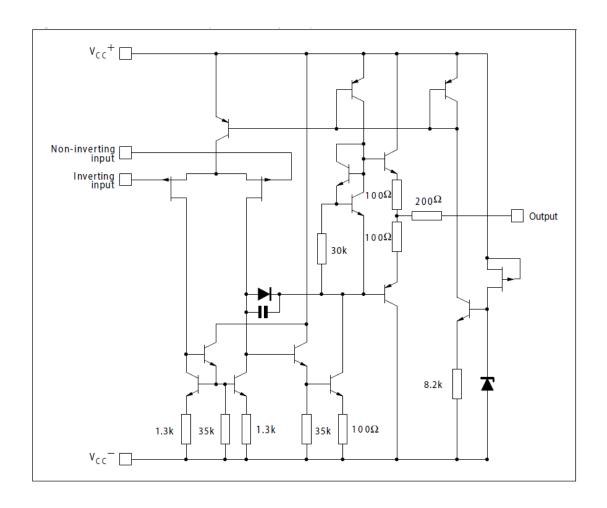


LM2901





TL084





6.2 **Tests Description**

Test name	Description	Purpose				
Die Oriented						
HTOL High Temperature Operating Life HTB High Temperature Bias	The device is stressed in static or dynamic configuration, approaching the operative max. absolute ratings in terms of junction temperature and bias condition.	To determine the effects of bias conditions and temperature on solid state devices over time. It simulates the devices' operating condition in an accelerated way. The typical failure modes are related to, silicon degradation, wire-bonds degradation, oxide faults.				
HTRB High Temperature Reverse Bias HTFB / HTGB High Temperature Forward (Gate) Bias	The device is stressed in static configura- tion, trying to satisfy as much as possible the following conditions: low power dissipation; max. supply voltage compatible with diffu- sion process and internal circuitry limita- tions;	To determine the effects of bias conditions and temperature on solid state devices over time. It simulates the devices' operating condition in an accelerated way. To maximize the electrical field across either reverse-biased junctions or dielectric layers, in order to investigate the failure modes linked to mobile contamination, oxide ageing, layout sensitivity to surface effects.				
HTSL High Temperature Storage Life	The device is stored in unbiased condition at the max. temperature allowed by the pack- age materials, sometimes higher than the max. operative temperature.	To investigate the failure mechanisms activated by high temperature, typically wire-bonds sol- der joint ageing, data retention faults, metal stress-voiding.				
ELFR Early Life Failure Rate	The device is stressed in biased conditions at the max junction temperature.	To evaluate the defects inducing failure in early life.				
Package Oriented						
PC Preconditioning	The device is submitted to a typical temperature profile used for surface mounting devices, after a controlled moisture absorption.	As stand-alone test: to investigate the moisture sensitivity level. As preconditioning before other reliability tests: to verify that the surface mounting stress does not impact on the subsequent reliability performance. The typical failure modes are "pop corn" effect and delamination.				
AC Auto Clave (Pressure Pot)	The device is stored in saturated steam, at fixed and controlled conditions of pressure and temperature.	To investigate corrosion phenomena affecting die or package materials, related to chemical contamination and package hermeticity.				
TC Temperature Cy- cling	The device is submitted to cycled temperature excursions, between a hot and a cold chamber in air atmosphere.	To investigate failure modes related to the thermo-mechanical stress induced by the different thermal expansion of the materials interacting in the die-package system. Typical failure modes are linked to metal displacement, dielectric cracking, molding compound delamination, wire-bonds failure, die-attach layer degradation.				



Test name	Description	Purpose					
TF / IOL Thermal Fatigue / Intermittent Operating Life	The device is submitted to cycled temperature excursions generated by power cycles (ON/OFF) at T ambient.	To investigate failure modes related to the thermo-mechanical stress induced by the different thermal expansion of the materials interacting in the die-package system. Typical failure modes are linked to metal displacement, dielectric cracking, molding compound delamination, wire-bonds failure, die-attach layer degradation.					
THB Temperature Humidity Bias	The device is biased in static configuration minimizing its internal power dissipation, and stored at controlled conditions of ambi- ent temperature and relative humidity.	To evaluate the package moisture resistance with electrical field applied, both electrolytic and galvanic corrosion are put in evidence.					
Other	Other						
ESD Electro Static Dis- charge	The device is submitted to a high voltage peak on all his pins simulating ESD stress according to different simulation models. CBM: Charged Device Model HBM: Human Body Model MM: Machine Model	To classify the device according to his susceptibility to damage or degradation by exposure to electrostatic discharge.					
LU Latch-Up	The device is submitted to a direct current forced/sunk into the input/output pins. Removing the direct current no change in the supply current must be observed.	To verify the presence of bulk parasitic effect inducing latch-up.					



Public Products List

PCN Title: Product Change Notification on new material set in ST Bouskoura for AMS products in SO8 and SO14 packages

PCN Reference: AMS/15/9514
PCN Created on: 06-Nov-2015

Subject: Public Products List

Dear Customer,

Please find below the Standard Public Products List impacted by the change.

TS512IDT	LM324D	TS3704IDT
TS556IDTTR	LM201ADT	TS922ID
UA741CDT	TSV358IDT	STM818MM6F
TSV622IDT	LM239DT	MC3303DT
TS9224IDT	LM258D	TL082ID
LMV822AIDT	TL072CDT	TS27L4AIDT
LMX358IDT	LM393DT	LM2901DT
TS339IDT	TS462CDT	TL072CD
LM833DT	TSV6392AIDT	LM224D
LMV393IDT	TS339CDT	TS944IDT
LM358DT	TS912AIDT	TS922AIDT
TS831-4IDT	TL074ACDT	LM2903D
TL061CDT	TSV854AIDT	STM818LM6F
TSV992AIDT	MC4558CDT	TS861AIDT
LM2904D	LM2901D	LMV324IDT
TS951IDT	LM193DT	TS912BIDT
LM2902DT	LMV358IDT	TS1852IDT
LM2904DT	TSC102IDT	TL084CD
TS954IDT	TS27L2AIDT	TS272IDT
TL082CD	TS271CDT	TSV911AIDT
LM393WDT	LM293DT	TL084CDT
TS461CDT	TS393CDT	LM248DT
TS1871IDT	LM324DT	TSV854IDT
STM706PAM6F	TS912IDT	TS1872IDT
LMV824IDT	LM339AD	TL074BCDT
TS514AIDT	TL084AIDT	M41T81SM6F
TL062CD	TL074CD	STM708SAM6F
TSV912IDT	LM339D	TL071CDT
LM339EDT	LF353DT	LM324AD
LMV822IDT	TL084BIDT	TS1874AIDT
TS861IDT	TSV912AIDT	STM805TM6F
TS924IDT	TS27M4IDT	TS274AIDT
TS393IDT	M41T0M6F	TS514AID
LM334DT	LM319DT	TSV992IDT
TS921ID	TS3022IDT	TSH22IDT
TL082ACDT	TS27L4CDT	LM258WDT
M41T82SM6F	TL082IDT	LM293D

TS942IDT	TS1851IDT	TS274ACDT
TL064ACDT	LM211D	LF253DT
LM293ADT	LM358ADT	MC33171DT
TS831-3IDT	TSV6292IDT	TSV914AIDT
TS374CDT	TS932IDT	TS864IDT
STM707M6F	MC33172DT	TS922AID
TS912ID	TS272BIDT	LM219DT
LM224ADT	TS942AIDT	UA741IDT
TS924AIDT	TS27L2ACDT	TS3702IDT
TS512AIDT	M41T56M6F	TL062IDT
TS274IDT	TSV6392IDT	STM805SM6F
TL064CD	TJM4558CDT	LM358AD
TL074ID	MC33172D	TS972IDT
TS952IDT	LM224DT	LF347DT
TS27L2AID	TS831-5ID	MC3403DT
M41T00M6F	MC1458ID	TL072ACDT
LM235D	STM708TAM6F	TSV324IDT
TL084IDT	TL072IDT	TS272AIDT
TS3704CDT	TS921IDT	LMV824AIDT
TS27L2IDT	LM324ADT	STM805LM6F
TL081CDT	TS831-5IDT	TL082BCDT
TL064CDT	LM258DT	LM2904WHDT
MC33174DT	TSV358AIDT	LM235DT
TL061IDT	STM692AM6F	TSV612AIDT
TSV632AIDT	TS332IDT	MC33174D
TS27L4IDT	TL071IDT	TSC103IDT
TL074CDT	LM393D	TS27L2CD
LF247DT	STM819MM6F	STM706TAM6F
TS272CDT	LM2903DT	TS274CDT
LM311DT	TS884IDT	STM802TM6F
TSV632IDT	TL062ID	M41T81M6F
STM704RM6F	TSV622AIDT	TL072BIDT
MC33078D	TSX9292IDT	LM211DT
TL082CDT	M41T00SM6F	TSV994AIDT
TS934IDT	TS944AIDT	TS27M4CDT
TSV911IDT	TS1854IDT	TS272ACDT
TS971IDT	TL074IDT	TS924ID
TS522IDT	TL081IDT	MC33078DT
LM158WDT	TS922IDT	LM258ADT
STM804TM6F	LM324WDT	LF351DT
LM2903WDT	LM239ADT	LM335DT
TS862IDT	STM706M6F	STM690SM6F
MC4558IDT	LM339DT	LM2904WDT
TS1872AIDT	LM358D	MC33079DT
TS372IDT	LM335ADT	LM158DT
LM335D	LM393EDT	TL064IDT
TL062CDT	STTS75M2F	TL084BCDT
TS27M2CDT	LM311D	TS482IDT
TS3702CDT	LM2902D	LMV339IDT
UA741ID	TSV612IDT	TS464CDT
•	•	



TL062ACDT	TS514IDT	TL062BCDT
LM393ADT	STM690AM6F	STM708M6F
STM705M6F	M41T80M6F	TS507IDT
TS524IDT	LM324EDT	TSV6192AIDT
STM708SM6F	TS9222IDT	STM706RM6F
STM804RM6F	LF347D	LMV324LIDT
STM802SM6F	TS372CDT	LMX324IDT
TS931IDT	TSV914IDT	TL061ACDT
TSX3702IDT	STM704TM6F	TSC1031IDT
STM703M6F	LM358AWDT	TS334IDT
LM124DT	STM805RM6F	M41T82RM6F
STM806RM6F	TSV6192IDT	TSX922IDT
TS27L2CDT	TSV6292AIDT	LS204CDT
STM706TM6F	LM139ADT	STM806SM6F
STM706SM6F	TS974IDT	TS27L2BIDT
LM339ADT	LM234DT	M41T11M6F
TL084ACDT	STM706PM6F	STM804SM6F
STM690RM6F	LM239D	TSV994IDT
STM708RAM6F	LM139DT	MC1458DT
STM795TM6F	TSH24IDT	LM358WDT
M41T82ZM6F	TS374IDT	LMV358LIDT
STLM75M2F	TSV852AIDT	STM802LM6F
LM335AD	MC33079D	STM806TM6F
STM795RM6F	STM817LM6F	STM704SM6F
LF351D	UA741CD	STM802RM6F
STM795SM6F	TS555IDTTR	TS834-5IDT
STM706AM6F	M41T01M6F	LM258AWDT
TSV852IDT	STM704M6F	STM813LM6F
STM819LM6F	STM704M6E	STM708TM6F
STM817MM6F	STM708RM6F	STM690TM6F
STM802MM6F	STM706RAM6F	

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